

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d



October 2014

## CNY171M, CNY172M, CNY173M, CNY174M, CNY17F1M, CNY17F2M, CNY17F3M, CNY17F4M, MOC8106M 6-Pin DIP High BV<sub>CEO</sub> Phototransistor Optocouplers

#### Features

- High BV<sub>CEO</sub>: 70 V Minimum (CNY17XM, CNY17FXM, MOC8106M)
- Closely Matched Current Transfer Ratio (CTR) Minimizes Unit-to-Unit Variation
- Current Transfer Ratio In Select Groups
- Very Low Coupled Capacitance Along With No Chip-to-Pin 6 Base Connection for Minimum Noise Susceptability (CNY17FXM, MOC8106M)
- Safety and Regulatory Approvals:
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

#### Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs
- Appliance Sensor Systems
- Industrial Controls

### Description

The CNY17XM, CNY17FXM, and MOC8106M devices consist of a gallium arsenide infrared emitting diode coupled with an NPN phototransistor in a dual in-line package.

#### **Package Outlines**

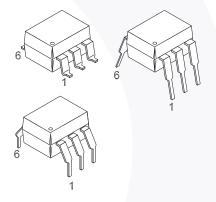
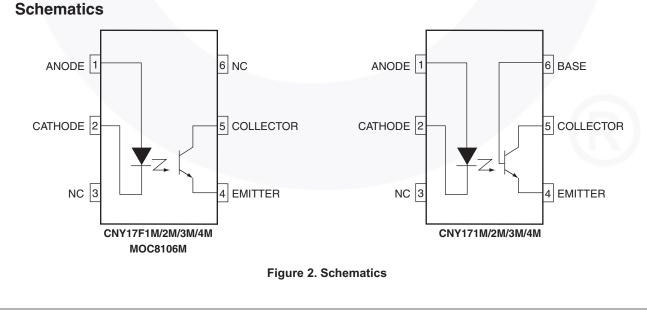


Figure 1. Package Outlines



CNY17XM, CNY17FXM, MOC8106M — 6-Pin DIP High BV<sub>CEO</sub> Phototransistor Optocouplers

### Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with t <sub>m</sub> = 10 s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
VIORM	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
Τ <sub>S</sub>	Case Temperature <sup>(1)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	350	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	800	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , $V_{IO}$ = 500 V <sup>(1)</sup>	> 10 <sup>9</sup>	Ω

Note:

1. Safety limit values - maximum values allowed in the event of a failure.

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units
TOTAL DE	VICE		
T <sub>STG</sub>	Storage Temperature	-40 to +125	°C
T <sub>A</sub>	Ambient Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 seconds	°C
	Total Device Power Dissipation @ 25°C (LED plus detector)	270	mW
PD	Derate Linearly From 25°C	2.94	mW/°C
EMITTER			
I <sub>F</sub>	Continuous Forward Current	60	mA
V <sub>R</sub>	Reverse Voltage	6	V
l <sub>F</sub> (pk)	Forward Current – Peak (1 µs pulse, 300 pps)	1.5	А
P	LED Power Dissipation 25°C Ambient	120	mW
PD	Derate Linearly From 25°C	1.41	mW/°C
DETECTO	2		
Ι <sub>C</sub>	Continuous Collector Current	50	mA
V <sub>CEO</sub>	Collector-Emitter Voltage	70	V
V <sub>ECO</sub>	Emitter Collector Voltage	7	V
D	Detector Power Dissipation @ 25°C	150	mW
PD	Derate Linearly from 25°C	1.76	mW/°C

### **Electrical Characteristics**

 $T_A = 25^{\circ}C$  unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
EMITTER							
		I <sub>F</sub> = 10 mA	All Devices	1.0	1.15	1.50	V
$V_{F}$	Input Forward Voltage	I <sub>F</sub> = 60 mA	CNY17XM, CNY17FXM	1.0	1.35	1.65	V
CJ	Capacitance	V <sub>F</sub> = 0 V, f = 1.0 MHz	All Devices		18		pF
I <sub>R</sub>	Reverse Leakage Current V <sub>R</sub> = 6 V		All Devices		0.001	10	μA
DETECTO	DR						
	Breakdown Voltage						
$BV_{CEO}$	Collector-to-Emitter	I <sub>C</sub> = 1 mA, I <sub>F</sub> = 0	All Devices	70	100		V
BV <sub>CBO</sub>	Collector-to-Base	I <sub>C</sub> = 10 μA, I <sub>F</sub> = 0	CNY17XM	70	120		V
BV <sub>ECO</sub>	Emitter-to-Collector	I <sub>E</sub> = 100 μA, I <sub>F</sub> = 0	All Devices	7	10		V
	Leakage Current						
I <sub>CEO</sub>	Collector-to-Emitter	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0	All Devices		1	50	nA
I <sub>CBO</sub>	Collector-to-Base	V <sub>CB</sub> = 10 V, I <sub>F</sub> = 0	CNY17XM			20	nA
	Capacitance						
$C_{CE}$	Collector-to-Emitter	V <sub>CE</sub> = 0, f = 1 MHz	All Devices		8		pF
C <sub>CB</sub>	Collector-to-Base	V <sub>CB</sub> = 0, f = 1 MHz	CNY17XM		20		pF
C <sub>EB</sub>	Emitter-to-Base	V <sub>EB</sub> = 0, f = 1 MHz	CNY17XM		10		pF

#### **Transfer Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
COUPLE	)						
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	MOC8106M	50		150	%
CTR Current Transfer Ratio	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	CNY171M, CNY17F1M	40		80	%	
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY172M, CNY17F2M	63		125	%
	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY173M, CNY17F3M	100		200	%	
		I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5 V	CNY174M, CNY17F4M	160		320	%
Collector-Emitter		l <sub>C</sub> = 0.5 mA, l <sub>F</sub> = 5 mA	MOC8106M			0.4	V
V <sub>CE(SAT)</sub>	Saturation Voltage	I <sub>C</sub> = 2.5 mA, I <sub>F</sub> = 10 mA	CNY17XM/CNY17FXM		0.4		v

#### Electrical Characteristics (Continued)

 $T_A = 25^{\circ}C$  unless otherwise specified.

#### **AC Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Units
NON-SAT	URATED SWITC	CHING TIME					
t <sub>on</sub>	Turn-On Time	$I_{\rm C}$ = 2.0 mA, V <sub>CC</sub> = 10 V, R <sub>L</sub> = 100 Ω	All Devices		2.0	10.0	μs
t <sub>off</sub>	Turn-Off Time	$I_{\rm C}$ = 2.0 mA, V <sub>CC</sub> = 10 V, R <sub>L</sub> = 100 Ω	All Devices		3.0	10.0	μs
t <sub>d</sub>	Delay Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$	CNY17XM/CNY17FXM			5.6	μs
t <sub>r</sub>	Rise Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$	CNY17XM/CNY17FXM			4.0	μs
ts	Storage Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$	CNY17XM/CNY17FXM			4.1	μs
t <sub>f</sub>	Fall Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 75 $\Omega$	CNY17XM/CNY17FXM			3.5	μs
SATURA	TED SWITCHING	TIMES					
		$I_F$ = 20 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY171M/F1M			5.5	μs
t <sub>d</sub>	Delay Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			8.0	μs
		$I_F$ = 20 mA, V <sub>CC</sub> = 5 V, R <sub>L</sub> = 1 kΩ	CNY171M/F1M			4.0	μs
t <sub>r</sub>	Rise Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			6.0	μs
	/	$I_F$ = 20 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY171M/F1M			34.0	μs
t <sub>s</sub>	Storage Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			39.0	μs
		$I_F$ = 20 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY171M/F1M			20.0	μs
t <sub>f</sub>	Fall Time	$I_F$ = 10 mA, $V_{CC}$ = 5 V, $R_L$ = 1 k $\Omega$	CNY172M/3M/4M CNY17F2M/F3M/F4M			24.0	μs

#### **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC <sub>RMS</sub>
C <sub>ISO</sub>	Isolation Capacitance	V <sub>I-O</sub> = 0 V, f = 1 MHz		0.2		pF
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = ±500 VDC, T <sub>A</sub> = 25°C	10 <sup>11</sup>			Ω



100

1000

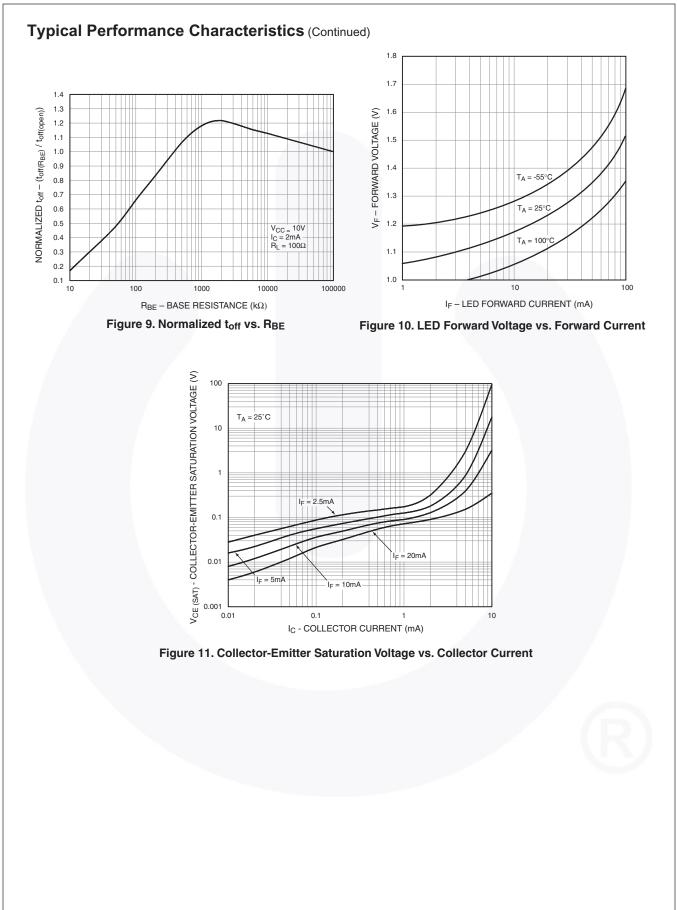
#### 1.6 $V_{CE} = 5.0 V$ $T_A = 25^{\circ}C$ Normalized to I<sub>F</sub> = 10 mA 1.2 1.4 $l_{\rm E} = 5 \, \rm{mA}$ 1.2 1.0 $I_F = 10 \text{ mA}$ NORMALIZED CTR 1.0 **NORMALIZED CTR** 0.8 0.8 $I_{\rm F} = 20 \, {\rm mA}$ 0.6 0.6 0.4 0.4 Normalized to: I<sub>F</sub> = 10 mA 0.2 T<sub>A</sub> = 25°C 0.2 0.0 -60 -40 -20 0 20 40 60 80 0 2 18 20 4 6 8 10 12 14 16 IF - FORWARD CURRENT (mA) T<sub>A</sub> – AMBIENT TEMPERATURE (°C) Figure 3. Normalized CTR vs. Forward Current Figure 4. Normalized CTR vs. Ambient Temperature 1.0 NORMALIZED CTR ( CTR<sub>RBE</sub> / CTR<sub>RBE</sub>(OPEN)) 1.0 NORMALIZED CTR ( CTR<sub>RBE</sub> / CTR<sub>RBE</sub>(OPEN)) 0.9 0.9 $I_F = 20 \text{ mA}$ 0.8 0.8 $I_{\rm F} = 10 \, {\rm m/}$ = 5 mA $V_{CF} = 0.3 V$ 0.7 0.7 20 n 0.6 0.6 0.5 0.5 = 10 mA IF. 0.4 0.4 0.3 0.3 $I_F = 5 \text{ mA}$ 0.2 0.2 V<sub>CE</sub> = 5.0 V 0.1 0.1 0.0 0.0 10 100 1000 10 100 $R_{BE}$ – BASE RESISTANCE (k $\Omega$ ) $R_{BE} - BASE RESISTANCE (k\Omega)$ Figure 5. CTR vs. RBE (Unsaturated) Figure 6. CTR vs. RBE (Saturated) 1000 $I_F = 10 \text{ mA}$ $V_{CC} = 10 \text{ V}$ $T_A = 25^{\circ}\text{C}$ 5.0 100 $V_{CC} = 10 V$ $I_{C} = 2 mA$ $R_{L} = 100 \Omega$ $\mathsf{NORMALIZED} \ t_{\mathsf{on}} - (t_{\mathsf{on}(\mathsf{R}_{\mathsf{BE}})} \ / \ t_{\mathsf{on}(\mathsf{open})})$ 4.5 SWITCHING SPEED (µs) 4.0 10 3.5 3.0 Т 2.5 T<sub>r</sub> 2.0 1.5 1.0 0.1 0.5 **L** 10 0.1 10 100 100 1000 10000 R – LOAD RESISTOR (kΩ) $R_{BE}$ – BASE RESISTANCE (k $\Omega$ ) Figure 8. Normalized ton vs. RBE Figure 7. Switching Speed vs. Load Resistor

1.4

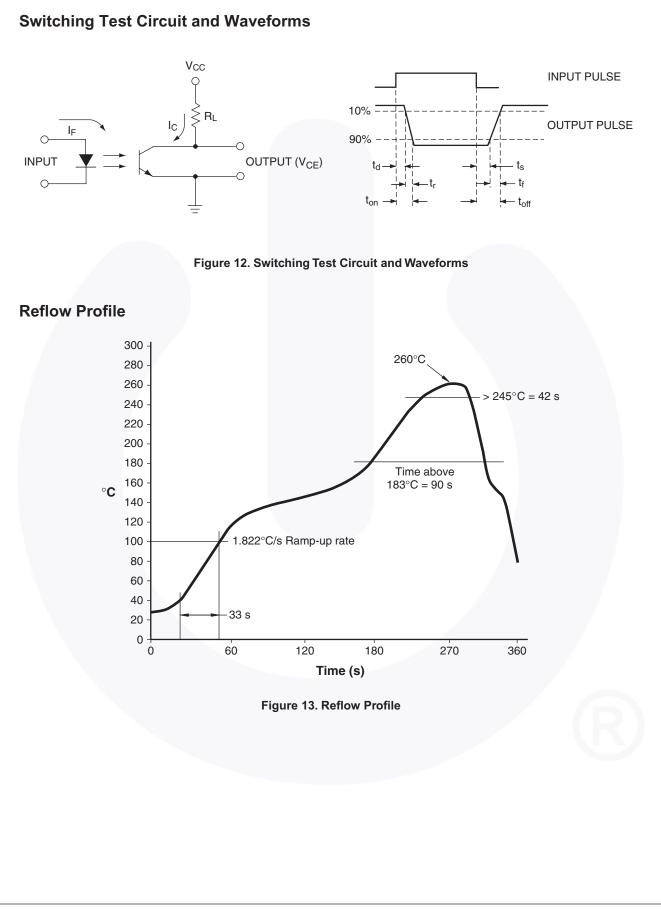
©2006 Fairchild Semiconductor Corporation CNY17XM, CNY17FXM, MOC8106M Rev. 1.1.2

**Typical Performance Characteristics** 

100000



7



### **Ordering Information**

Part Number	Package	Packing Method
CNY171M	DIP 6-Pin	Tube (50 Units)
CNY171SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
CNY171SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
CNY171TM	DIP 6-Pin, 0.4" Lead Spacing	Tube (50 Units)
CNY171VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
CNY171SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
CNY171SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
CNY171TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

#### Note:

2. The product orderable part number system listed in this table also applies to the CNY17FXM product family and the MOC8106M device.

#### Marking Information

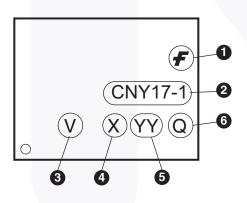
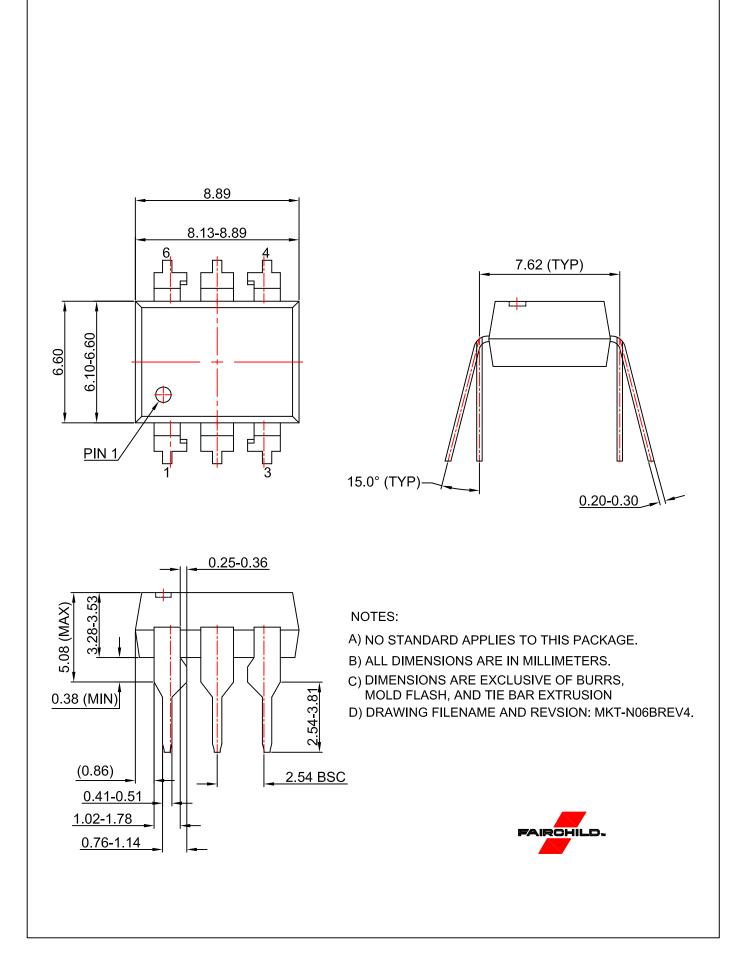
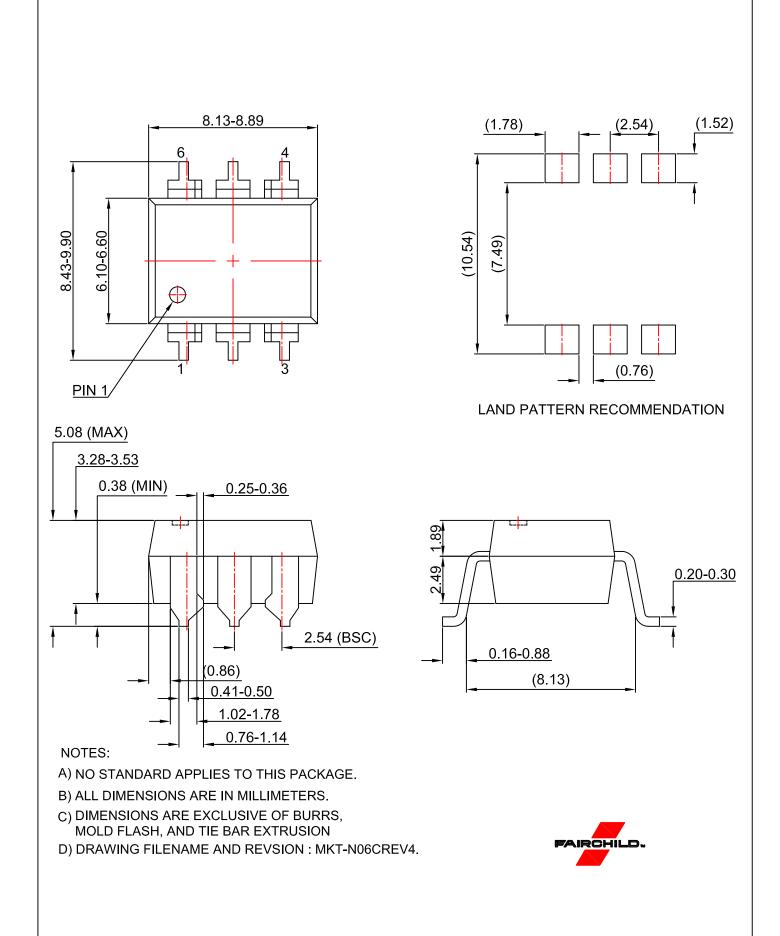


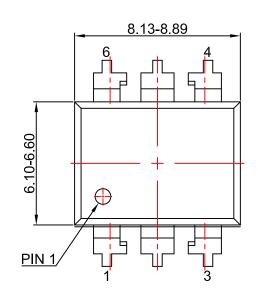
Figure 14. Top Mark

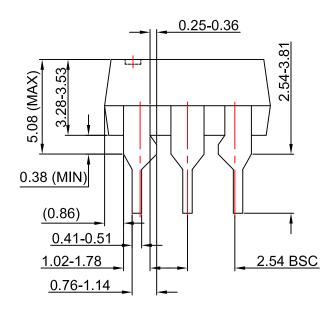
#### Table 1. Top Mark Definitions

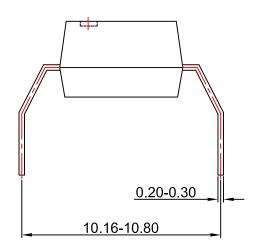
1	Fairchild Logo		
2	Device Number		
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)		
4	One-Digit Year Code, e.g., "4"		
5	Digit Work Week, Ranging from "01" to "53"		
6	Assembly Package Code		











#### NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVSION: MKT-N06Drev4





\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT <u>HTTP://WWW.FAIRCHILDSEMI.COM</u>, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### AUTHORIZED USE

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Terms of Use

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### **PRODUCT STATUS DEFINITIONS**

Definition of Terms		
Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 177

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor: CNY171TVM CNY171SM CNY171VM CNY171SR2M CNY171M CNY171SVM CNY171SR2VM